

BF545A; BF545B; BF545C

N-channel silicon junction field-effect transistors Rev. 4 — 15 September 2011 Proc

Product data sheet

Product profile

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage (max. 2.2 V for BF545A).

1.3 Applications

- Impedance converters in e.g. electret microphones and infra-red detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage		-	-	±30	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 1 \mu A; V_{DS} = 15 V$	-0.4	-	-7.8	V
I_{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF545A	2	-	6.5	mA
		BF545B	6	-	15	mA
		BF545C	12	-	25	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	-	-	250	mW
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	3	-	6.5	mS



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)	3	g → d s
3	gate (g)	1 2	sym054

3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BF545A	-	plastic surface mounted package; 3 leads	SOT23				
BF545B							
BF545C							

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
BF545A	20*
BF545B	21*
BF545C	22*

^{[1] * =} p: made in Hong Kong.

^{* =} t: made in Malaysia.

^{* =} W: made in China.

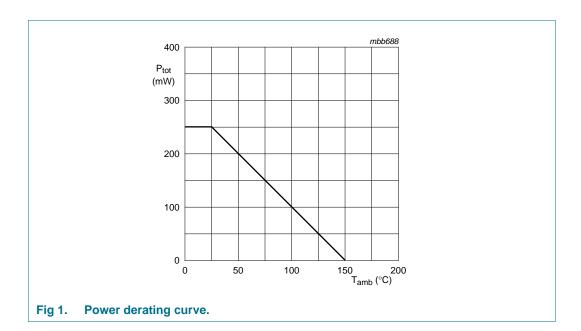
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±30	V
V_{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
I_{G}	forward gate current (DC)		-	10	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u>	500	K/W

^[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

7. Static characteristics

Table 7. Static characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = -1 \mu A; V_{DS} = 0 V$	-30	-	-	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \mu A; V_{DS} = 15 V$				
		BF545A	-0.4	-	-2.2	V
		BF545B	-1.6	-	-3.8	V
		BF545C	-3.2	-	-7.8	V
		$I_D = 1 \mu A; V_{DS} = 15 V$	-0.4	-	-7.5	V
I _{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF545A	2	-	6.5	mΑ
		BF545B	6	-	15	mΑ
		BF545C	12	-	25	mA
I _{GSS}	gate-source leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-0.5	-1000	pА
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V};$ $T_j = 125 ^{\circ}\text{C}$	-	-	-100	nA
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	3	-	6.5	mS
y _{os}	common source output admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	40	-	μS

8. Dynamic characteristics

Table 8. Dynamic characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		$V_{GS} = -10 \text{ V}$	-	1.7	-	pF
		V _{GS} = 0 V	-	3	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		V _{GS} = -10 V	-	0.8	-	pF
		V _{GS} = 0 V	-	0.9	-	pF
- -	common source input conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
		f = 100 MHz	-	15	-	μS
		f = 450 MHz	-	300	-	μS
9 _{fs}	common source transfer	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
conducta	conductance	f = 100 MHz	-	2	-	mS
		f = 450 MHz	-	1.8	-	mS
g _{rs}	common source reverse	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
gos	common source output	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS

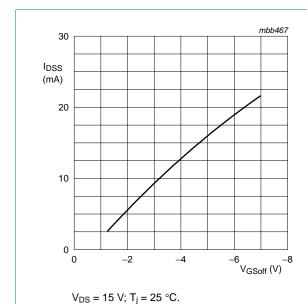
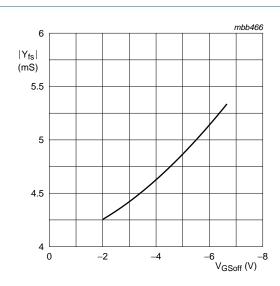
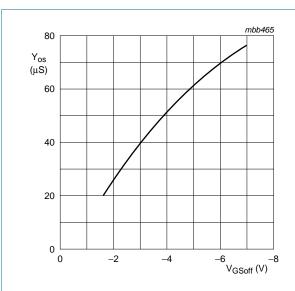


Fig 2. Drain current as a function of gate-source cut-off voltage; typical values.



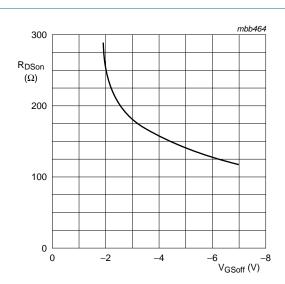
 V_{DS} = 15 V; V_{GS} = 0 V; T_j = 25 °C.

Fig 3. Forward transfer admittance as a function of gate-source cut-off voltage; typical values.



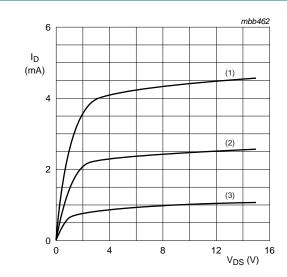
 V_{DS} = 15 V; V_{GS} = 0 V; T_j = 25 °C.

Fig 4. Common-source output admittance as a function of gate-source cut-off voltage; typical values.



 V_{DS} = 100 mV; V_{GS} = 0 V; T_j = 25 °C.

Fig 5. Drain-source on-resistance as a function of gate-source cut-off voltage; typical values.

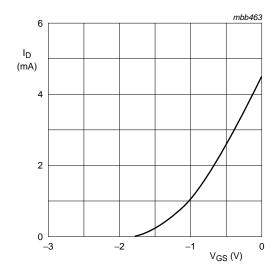


BF545A

$$T_i = 25 \, ^{\circ}C$$
.

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$

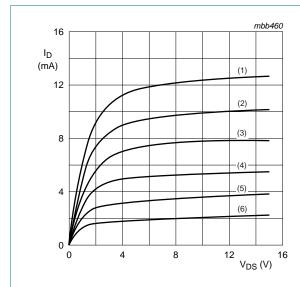
Fig 6. Typical output characteristics.



BF545A

 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

Fig 7. Typical input characteristics.

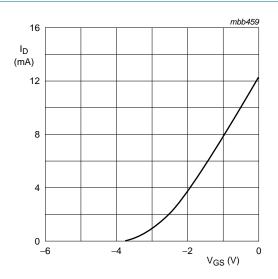


BF545B

$$T_i = 25 \, ^{\circ}C$$
.

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$
- (4) $V_{GS} = -1.5 \text{ V}.$
- (5) $V_{GS} = -2.0 \text{ V}.$
- (6) $V_{GS} = -2.5 \text{ V}.$

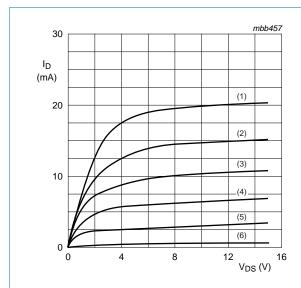
Fig 8. Typical output characteristics.



 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

BF545B

Fig 9. Typical input characteristics.

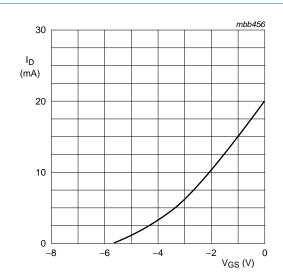


BF545C

 $T_i = 25 \, ^{\circ}C$.

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -1.0 \text{ V}.$
- (3) $V_{GS} = -2.0 \text{ V}.$
- (4) $V_{GS} = -3.0 \text{ V}.$
- (5) $V_{GS} = -4.0 \text{ V}.$
- (6) $V_{GS} = -5.0 \text{ V}.$

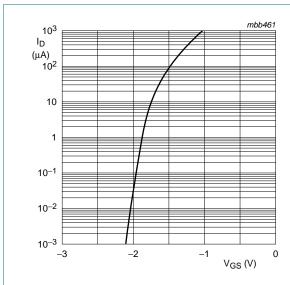
Fig 10. Typical output characteristics.



BF545C

 $V_{DS} = 15 \text{ V}; T_j = 25 \,^{\circ}\text{C}.$

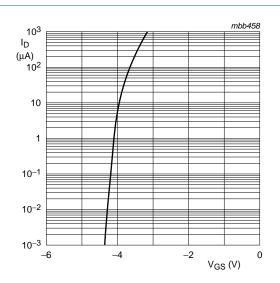
Fig 11. Typical input characteristics.



BF545A

 $V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$

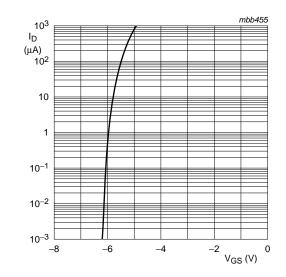
Fig 12. Drain current as a function of gate-source voltage; typical values.



BF545B

 $V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$

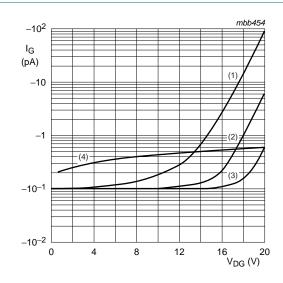
Fig 13. Drain current as a function of gate-source voltage; typical values.



BF545C

 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

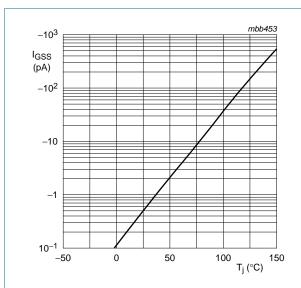
Fig 14. Drain current as a function of gate-source voltage; typical values.



 I_D = 10 mA only for BF545B and BF545C; T_j = 25 °C.

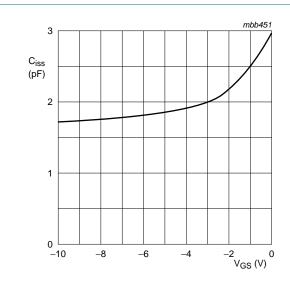
- (1) $I_D = 10 \text{ mA}.$
- (2) $I_D = 1 \text{ mA}.$
- (3) $I_D = 0.1 \text{ mA}.$
- (4) I_{GSS}.

Fig 15. Gate current as a function of drain-gate voltage; typical values.



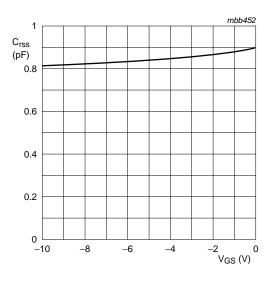
 $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}.$

Fig 16. Gate current as a function of junction temperature; typical values.



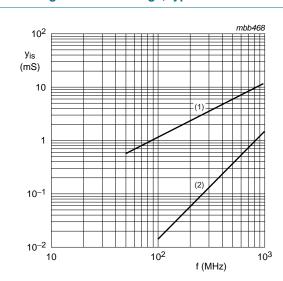
 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

Fig 18. Typical input capacitance.



 $V_{DS} = 15 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}.$

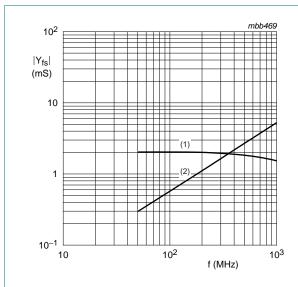
Fig 17. Reverse transfer capacitance as a function of gate-source voltage; typical values.



 $V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}; T_{amb} = 25 \text{ °C}.$

- (1) b_{is}.
- (2) g_{is}.

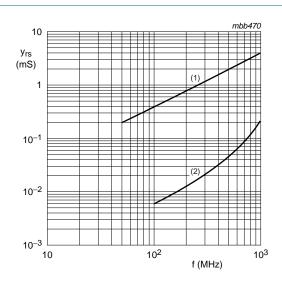
Fig 19. Common-source input admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) g_{fs}
- (2) $-b_{fs}$.

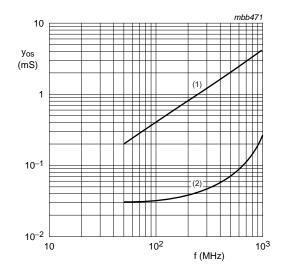
Fig 20. Common-source forward transfer admittance; typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}.$

- (1) $-b_{rs}$
- $(2) \quad -g_{rs}.$

Fig 21. Common-source reverse transfer admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{os}.
- (2) g_{os}.

Fig 22. Common-source output admittance; typical values.

9. Package outline

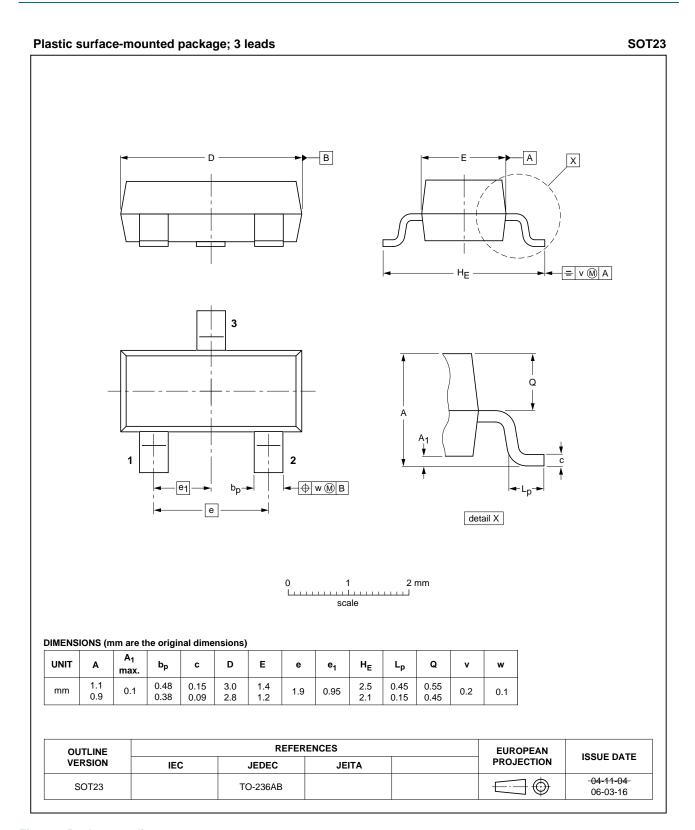


Fig 23. Package outline.

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF545A_BF545B_BF545C v.4	20110915	Product data sheet	-	BF545A_BF545B_BF545C v.3
Modifications:		of this data sheet has be of NXP Semiconductors.	•	comply with the new identity
	 Legal texts 	have been adapted to th	ne new company r	name where appropriate.
	 Package ou 	ıtline drawings have bee	n updated to the I	atest version.
BF545A_BF545B_BF545C v.3 (9397 750 13391)	20040805	Product data sheet	-	BF545A-B-C v.2
BF545A-B-C v.2	19960729	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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BF545A_BF545B_BF545C

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N-channel silicon junction field-effect transistors)

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For sales office addresses, please send an email to: salesaddresses@nxp.com

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.